42390.P7511

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Ali Keshavarzi et al.

Application No.: 09/469,406

Filed: December 22, 1999

For: DECOUPLING CAPACITORS FOR THIN GATE OXIDES

Examiner: Donghee Kang

Art Unit: 2811

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Washington, D.C. 20231

RESPONSE

Sir:

This is in response to the Office action dated August 13, 2002. Reconsideration of the application is requested. The claims are not amended in this response.

ENTIRE SET OF PENDING CLAIMS (Clean version)

29. A die, comprising:

a first conductor carrying a power supply voltage;

a second conductor carrying a ground voltage; and

a semiconductor decoupling capacitor to provide decoupling capacitance between the first and second conductors, the semiconductor decoupling capacitor including:

(a) a gate electrode coupled to the first conductor to receive the power supply voltage,

(b) a diffusion coupled to the second conductor to receiye the ground voltage, and

(c) a body to receive the ground voltage through the diffusion, the semiconductor decoupling capacitor thereby being in depletion mode.

FS.5 (30) The die of claim 29, wherein gate electrode is p-type and the diffusion and the